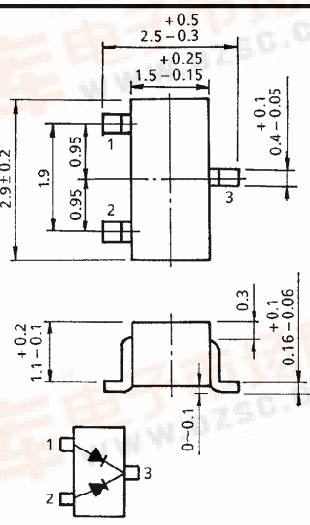
TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS321

LOW VOLTAGE HIGH SPEED SWITCHING.

Unit in mm

- Low Forward Voltage : $V_F = 0.42V$ (Typ.)
- Low Reverse Current : $I_R = 500nA$ (Max.)
- Small Package : SC-59 (SOT-23MOD)



1. ANODE 1
2. ANODE 2
3. CATHODE 1, 2

S-MINI	
JEDEC	TO-236MOD
EIAJ	SC-59
TOSHIBA	1-3G1F

Weight : 0.012g

MAXIMUM RATINGS (Ta = 25°C)

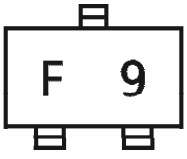
CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	12	V
Reverse Voltage	V_R	10	V
Maximum (Peak) Forward Current	I_{FM}	150 (*)	mA
Average Forward Current	I_O	50 (*)	mA
Surge Current (t = 10ms)	I_{FSM}	1000 (*)	mA
Power Dissipation	P	150	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55 ~ 125	°C

(*) Unit Rating. Total Rating = Unit Rating × 1.5.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	$I_F = 1mA$	—	0.32	—	V
	$V_{F(2)}$	$I_F = 10mA$	—	0.42	—	
	$V_{F(3)}$	$I_F = 50mA$	—	0.63	1.00	
Reverse Current	I_R	$V_R = 10V$	—	—	500	nA
Total Capacitance	C_T	$V_R = 0$, f = 1MHz	—	3.2	4.5	pF

MARKING



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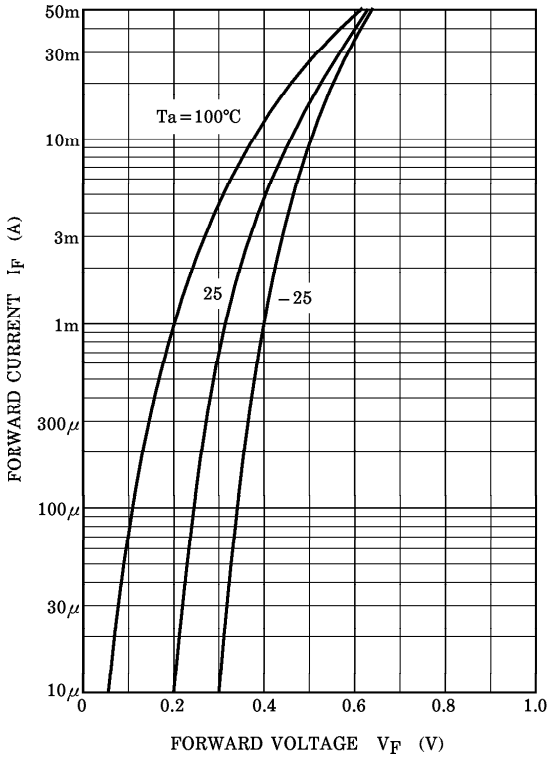
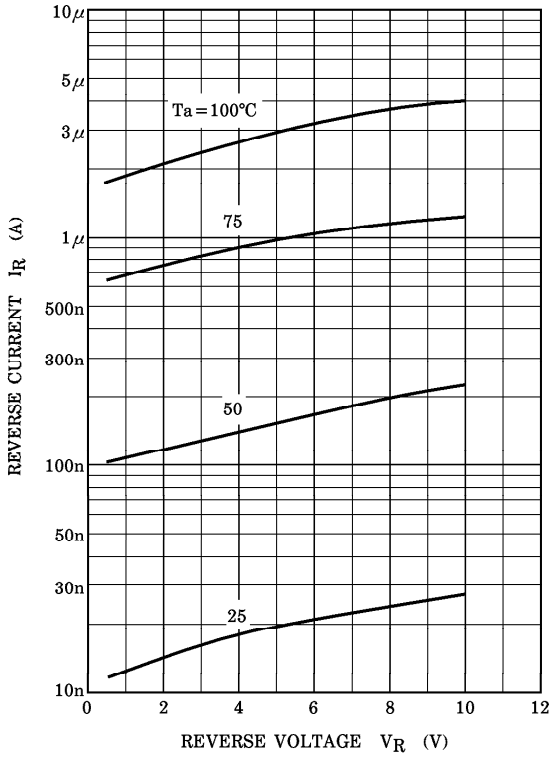
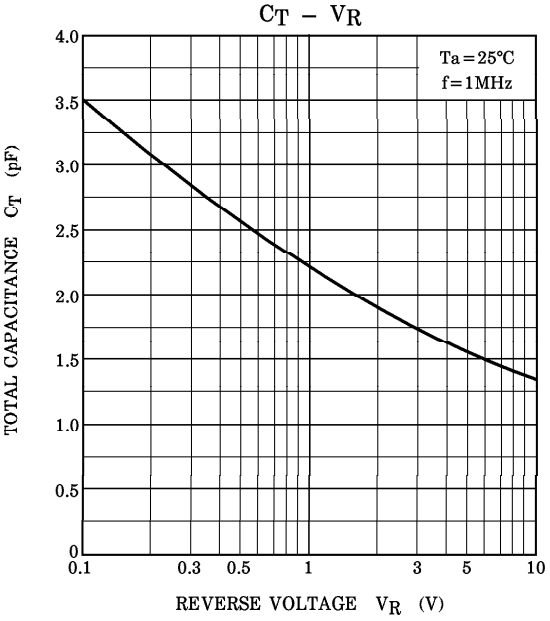
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



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